

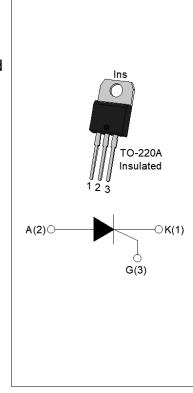


**JCT616A** 16A SCR

Rev.A.1.0

#### **DESCRIPTION:**

With high ability to withstand the shock loading of large current, JCT616A of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT616A provides a rated insulation voltage of 2500 V<sub>RMS</sub>, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.



#### **MAIN FEATURES**

Symbol	Value	Unit	
I <sub>T(RMS)</sub>	16	А	
V <sub>DRM</sub> /V <sub>RRM</sub>	600	V	
I <sub>GT</sub>	15	mA	

### **ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	T <sub>stg</sub>	-40-150	
Operating junction temperature range	Tj	-40-125	
Repetitive peak off-state voltage (T <sub>j</sub> =25 )	V <sub>DRM</sub>	600	V
Repetitive peak reverse voltage (T <sub>j</sub> =25 )	V <sub>RRM</sub>	600	V
Average on-state current (T <sub>C</sub> 76 )	I <sub>T(AV)</sub>	10	Α
RMS on-state current (Tc 76 )	I <sub>T(RMS)</sub>	16	Α
Non repetitive surge peak on-state current (t <sub>p</sub> =10ms, T <sub>j</sub> =25 )	Ітѕм	150	А
Non repetitive surge peak on-state current $(t_p=8.3\text{ms}, T_j=25)$		165	
$I^2$ t value for fusing ( $t_p=10$ ms , $T_j=25$ )	l <sup>2</sup> t	113	A <sup>2</sup> s
Critical rate of rise of on-state current (I <sub>G</sub> =2 I <sub>GT</sub> , f=100Hz , T <sub>j</sub> =125 )	dl/dt	150	A s

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## **JCT616A**

Peak gate current (t <sub>p</sub> =20 s , T <sub>j</sub> =125 )	I <sub>GM</sub>	5	А
Average gate power dissipation (T <sub>j</sub> =125 )	P <sub>G(AV)</sub>	1	W
Peak gate power	P <sub>GM</sub>	20	W
Peak pulse voltage (T <sub>j</sub> =25 ; non-repetitive,off-state;FIG.7)	V <sub>pp</sub>	0.5	kV

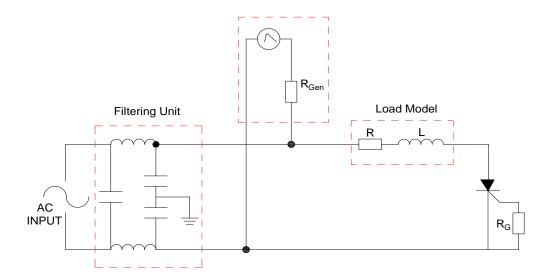
# $\textbf{ELECTRICAL CHARACTERISTICS} \ (T_{j}\!\!=\!\!25 \quad \text{ unless otherwise specified)}$

Cymhal	Toot Condition	Value			11:4:4		
	Symbol	Test Condition	MIN.	TYP.	MAX.	Unit	
	I <sub>GT</sub>	V- 40V D- 22	-	-	15	mA	
	V <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =33	-	-	1	V	
	V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125 R <sub>L</sub> =3.3K	0.2	_	-	_	

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FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.

IEC61000-4-5 Standards Surge Generator





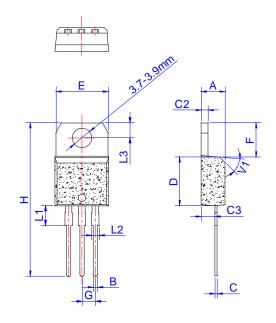
## **ORDERING INFORMATION**

Order code	Voltage V <sub>DRM</sub> /V <sub>RRM</sub> (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT616A	600	15	TO-220A(Ins)	50	Tube

## **Document Revision History**

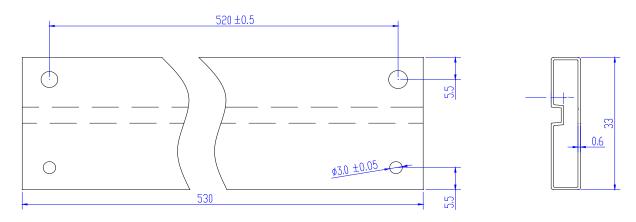
Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update

## PACKAGE MECHANICAL DATA



	Dimensions					
Ref.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	4.40		4.60	0.173		0.181
В	0.61		0.88	0.024		0.035
С	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.25		6.85	0.246		0.270
G	2.40		2.70	0.094		0.106
Н	28.0		29.8	1.102		1.173
L1	3.45		4.05	0.136		0.159
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

### **DELIVERY MODE**



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